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Edition 1.1



PRODUCT PROFILE

2SC2525, 2SC2526

Silicon High Speed Power Transistor

DESCRIPTION

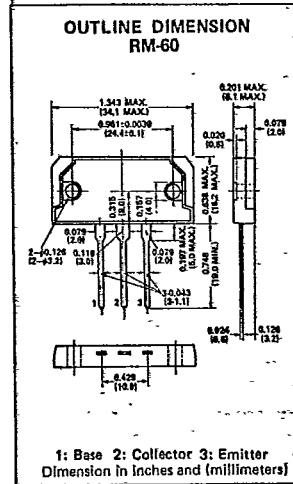
The 2SC2525/2SC2526 are silicon NPN general purpose, high power switching transistors fabricated with Fujitsu's unique Ring Emitter Transistor (RET) technology. RET devices are constructed with multiple emitters connected through diffused ballast resistors which provide uniform current density. This structure permits the design of high power transistors with exceptional switching characteristics and frequency response in high current applications.

The 2SC2525/2SC2526 are especially well-suited for High frequency power amplifiers, Audio power amplifiers, Switching regulators and DC-DC Converters. PNP complements, 2SA 1075/2SA 1076, are available.

- High  $f_T = 80$  MHz (typ)
- Ultra fast switching speed
- Excellent Safe Operating Area
- Improved reverse Second-Breakdown Capability

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value		Unit
		2SC 2525	2SC 2526	
Collector to Base Voltage	$V_{CBO}$	120	160	V
Emitter to Base Voltage	$V_{EBO}$	7	7	V
Collector to Emitter Voltage	$V_{CEO}$	120	160	V
Collector Current	$I_C$	12	12	A
Collector Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_C$	120	120	W
Junction Temperature	$T_J$	+150		$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 ~ +150		$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Test Conditions	Limits						Unit
			2SC 2525			2SC 2526			
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 120V/160V, I_E = 0$	-	-	50/-	-	-	-/50	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 7V, I_C = 0$	-	-	50	-	-	50	$\mu\text{A}$
Collector Cutoff Current	$I_{CEO}$	$V_{CE} = 120V/160V, R_{BE} = \infty$	-	-	1/-	-	-	-/1	mA
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu\text{A}, I_E = 0$	120	-	-	160	-	-	V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu\text{A}, I_C = 0$	7	-	-	7	-	-	V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	120	-	-	160	-	-	V
DC Current Gain	$h_{FE1}$	$V_{CE} = 5V, I_C = 1A$	60	-	200	60	-	200	
DC Current Gain	$h_{FE2}$	$V_{CE} = 5V, I_C = 7A$	40	-	-	40	-	-	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5A, I_B = 0.5A$	-	0.7	1.8	-	0.7	1.8	V
Base to Emitter Voltage	$V_{BE}$	$V_{CE} = 5V, I_C = 5A$	-	1.25	1.7	-	1.25	1.7	V
Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 1A, f = 10\text{MHz}$	60	80	-	60	80	-	MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1\text{MHz}$	-	180	300	-	180	300	pF
Rise Time	$t_r$	$I_C = 7.5A, R_L = 4\Omega$ $I_{B1} = -I_{B2} = 0.75A$	-	0.3	-	-	0.3	-	$\mu\text{s}$
Storage Time	$t_{stg}$		-	1.3	-	-	1.3	-	$\mu\text{s}$
Fall Time	$-t_f$		-	0.2	-	-	0.2	-	$\mu\text{s}$

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\* Pulsed: Pulse Width  $\leq 300\mu\text{s}$   
Duty Cycle  $\leq 6\%$